

N-channel TrenchMOS standard level FET 28 July 2016

**Product data sheet** 

### 1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

### 2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

### 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	75	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	96	W
Static charact	eristics					- 1	
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 11		-	5.6	7.2	mΩ
Dynamic char	acteristics	·					
Q <sub>GD</sub>	gate-drain charge	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; V <sub>DS</sub> = 32 V; Fig. 13; Fig. 14		-	7.4	-	nC

[1] Continuous current is limited by package.

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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UFA
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK768R1-40E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK768R1-40E	BUK768R1-40E

### 8. Limiting values

#### Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	96	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	75	А
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 2</u>	[1]	-	59	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	335	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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# **BUK768R1-40E**

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	75	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	335	А
Avalanche rug	Avalanche ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{split} I_D &= 75 \text{ A};  \text{V}_{\text{sup}} \leq 40 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \\ \text{V}_{\text{GS}} &= 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ \hline \text{Fig. 4} \end{split}$	[2][3]	-	43.8	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

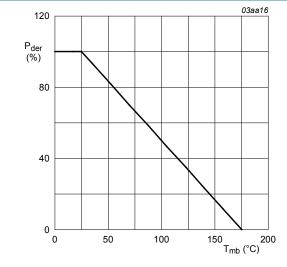
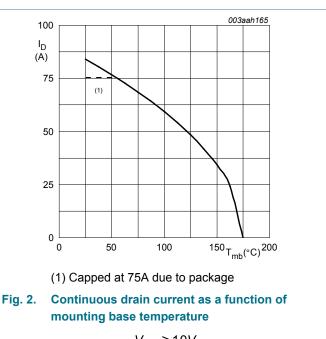


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

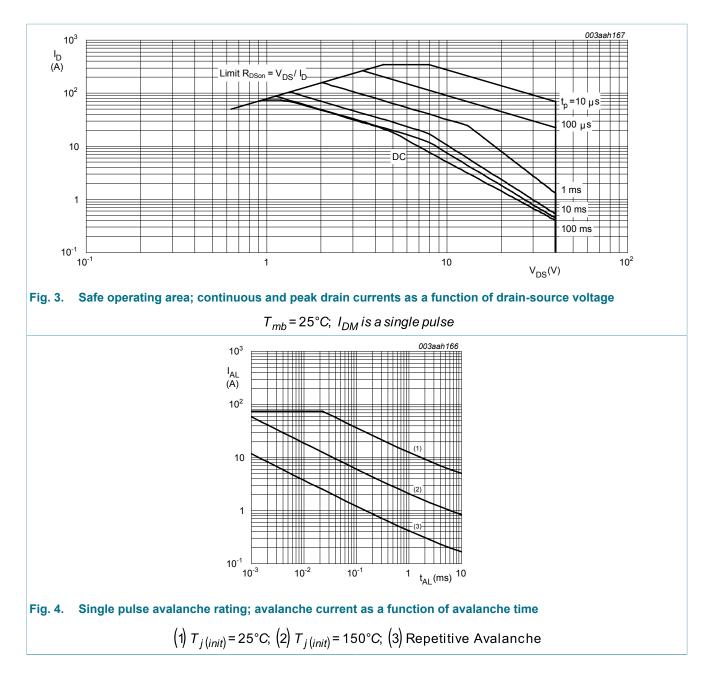


 $V_{GS} \ge 10V$ 



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### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

#### Table 6. Thermal characteristic

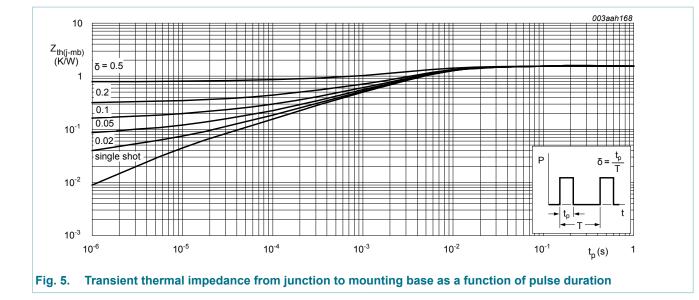
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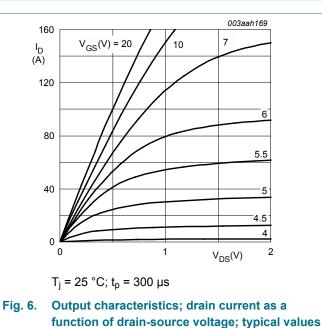
# **10.** Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · · · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	40	-	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	36	-	-	V
V <sub>GS(th)</sub> gate-source thresho voltage	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.5	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.05	1	μA
		$V_{DS}$ = 40 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	-	5.6	7.2	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 11	-	-	13.7	mΩ
Dynamic ch	naracteristics	· · · ·	· ·			
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 20 A; $V_{DS}$ = 32 V; $V_{GS}$ = 10 V;	-	24	-	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	5.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-	7.4	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
C <sub>iss</sub>	input capacitance	$V_{GS}$ = 0 V; $V_{DS}$ = 25 V; f = 1 MHz;	-	1300	1730	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	260	312	pF
C <sub>rss</sub>	reverse transfer capacitance		-	144	197	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.5 Ω; V <sub>GS</sub> = 10 V;	-	11	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	9	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	21	-	ns
t <sub>f</sub>	fall time		-	9	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to center of die	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bonding pad	-	7.5	-	nH
Source-dra	in diode			1		,
V <sub>SD</sub>	source-drain voltage	$I_{S}$ = 20 A; $V_{GS}$ = 0 V; $T_{j}$ = 25 °C; <u>Fig. 16</u>	-	0.86	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI_{S}/dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	18.6	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V	-	10.7	-	nC



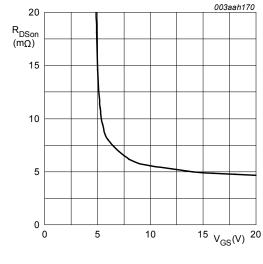


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

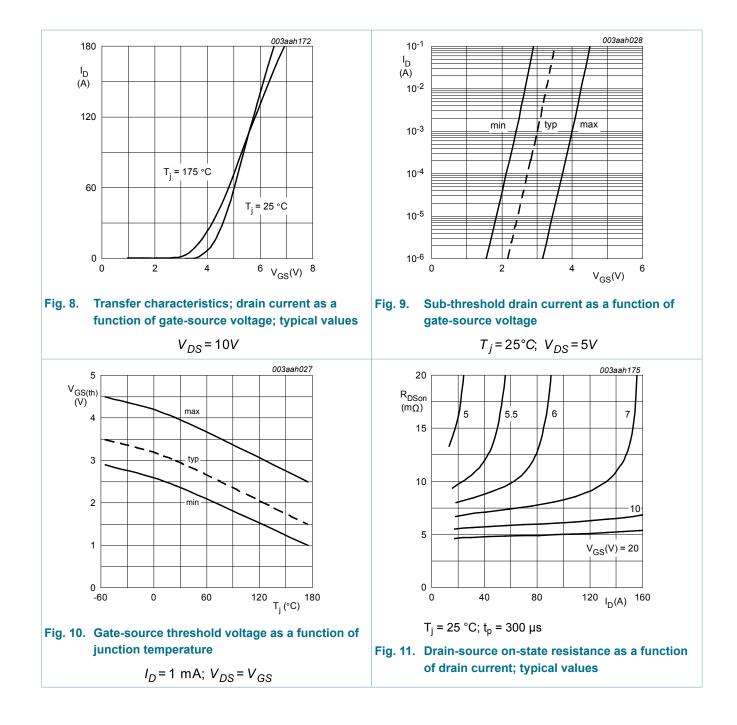
 $T_j = 25^{\circ}C; I_D = 20A$ 

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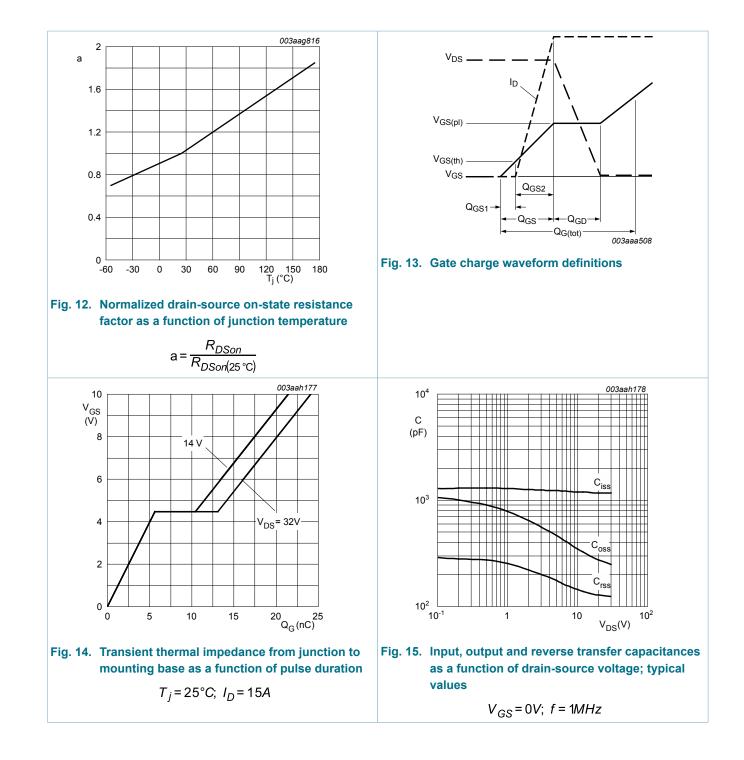
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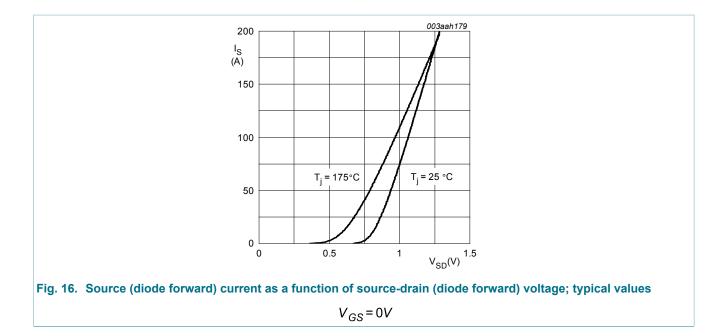
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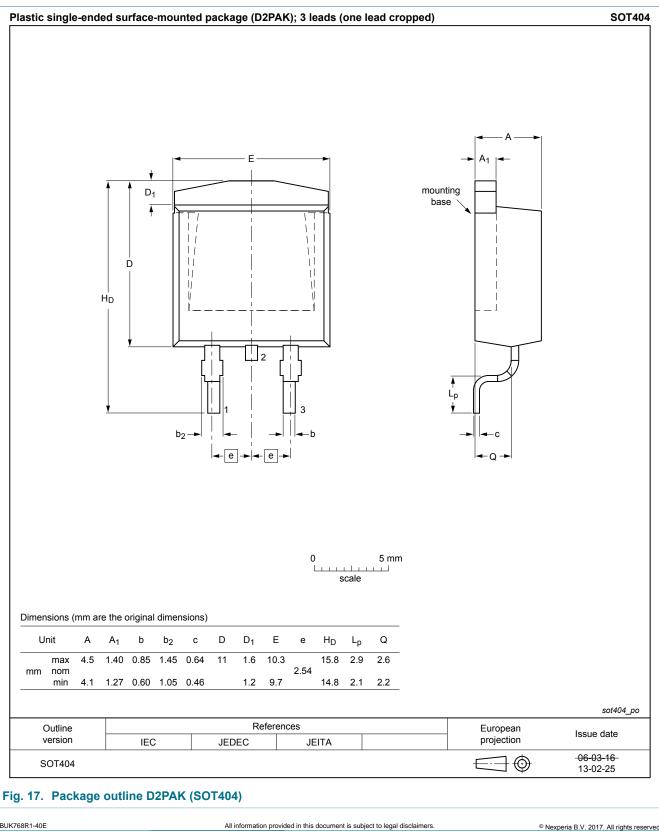
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## 11. Package outline



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### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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